

[NON-VOLATILE MEMORY CELL AND FABRICATION THEREOF]

Abstract

A non-volatile memory cell is described. The non-volatile memory cell comprises a substrate, a charge-trapping layer, a gate and a source/drain. The charge-trapping layer comprises an insulating layer and metal nano-particles contained therein, wherein the metal nano-particles are formed with thermal dissociation of an oxide of the same metal. The gate is disposed on the charge-trapping layer, and the source/drain is located in the substrate beside the gate.